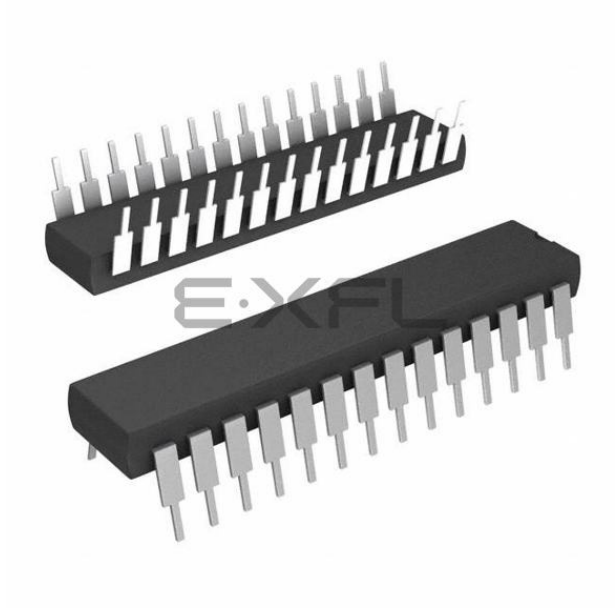

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	PIC
Core Size	8-Bit
Speed	64MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, HLVD, POR, PWM, WDT
Number of I/O	24
Program Memory Size	8KB (4K x 16)
Program Memory Type	FLASH
EEPROM Size	256 x 8
RAM Size	512 x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 11x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Through Hole
Package / Case	28-DIP (0.300", 7.62mm)
Supplier Device Package	28-SPDIP
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic18f23k20-i-sp

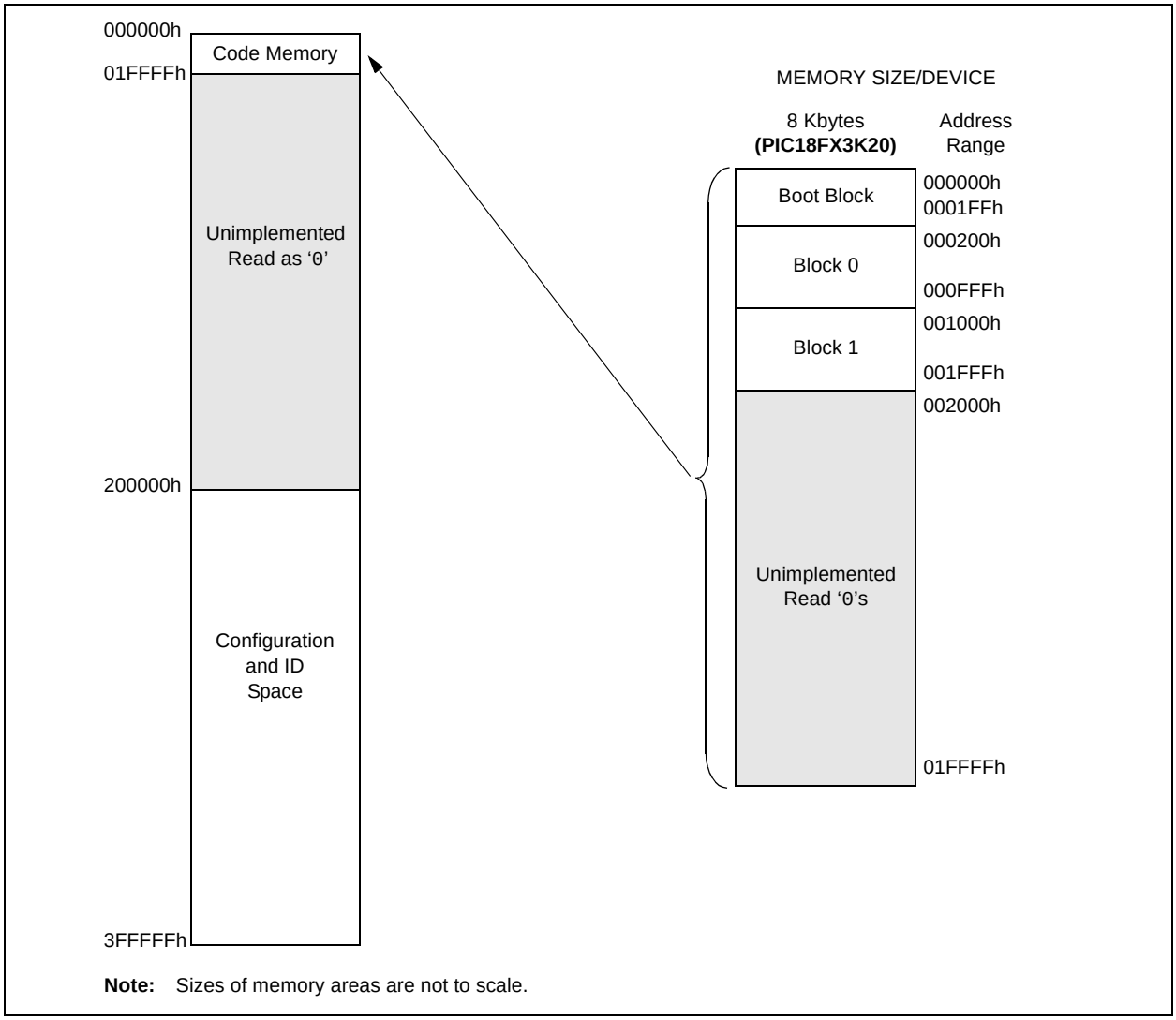
2.3 Memory Maps

For the PIC18FX3K20 devices, the code memory space extends from 0000h to 01FFFh (8 Kbytes) in two 4-Kbyte blocks. Addresses 0000h through 01FFh, however, define a “Boot Block” region that is treated separately from Block 0. All of these blocks define code protection boundaries within the code memory space.

TABLE 2-2: IMPLEMENTATION OF CODE MEMORY

Device	Code Memory Size (Bytes)
PIC18F23K20	000000h-001FFFh (8K)
PIC18F43K20	

FIGURE 2-6: MEMORY MAP AND THE CODE MEMORY SPACE FOR PIC18FX3K20 DEVICES

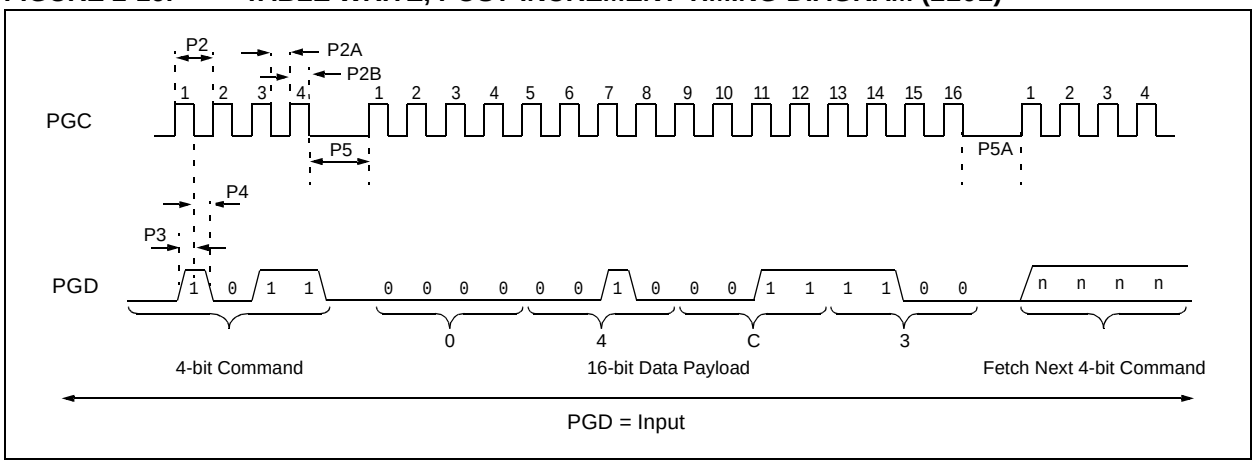


Note: Sizes of memory areas are not to scale.

TABLE 2-7: SAMPLE COMMAND SEQUENCE

4-Bit Command	Data Payload	Core Instruction
1101	3C 40	Table Write, post-increment by 2

FIGURE 2-16: TABLE WRITE, POST-INCREMENT TIMING DIAGRAM (1101)



3.0 DEVICE PROGRAMMING

Programming includes the ability to erase or write the various memory regions within the device.

In all cases, except high-voltage ICSP Bulk Erase, the EECON1 register must be configured in order to operate on a particular memory region.

When using the EECON1 register to act on code memory, the EEPGD bit must be set (EECON1<7> = 1) and the CFGS bit must be cleared (EECON1<6> = 0). The WREN bit must be set (EECON1<2> = 1) to enable writes of any sort (e.g., erases) and this must be done prior to initiating a write sequence. The FREE bit must be set (EECON1<4> = 1) in order to erase the program space being pointed to by the Table Pointer. The erase or write sequence is initiated by setting the WR bit (EECON1<1> = 1). It is strongly recommended that the WREN bit only be set immediately prior to a program or erase.

3.1 ICSP Erase

3.1.1 HIGH-VOLTAGE ICSP BULK ERASE

Erasing code or data EEPROM is accomplished by configuring two Bulk Erase Control registers located at 3C0004h and 3C0005h. Code memory may be erased portions at a time, or the user may erase the entire device in one action. Bulk Erase operations will also clear any code-protect settings associated with the memory block erased. Erase options are detailed in Table 3-1. If data EEPROM is code-protected (CPD = 0), the user must request an erase of data EEPROM (e.g., 0084h as shown in Table 3-1).

TABLE 3-1: BULK ERASE OPTIONS

Description	Data (3C0005h:3C0004h)
Chip Erase	0F8Fh
Erase User ID	0088h
Erase Data EEPROM	0084h
Erase Boot Block	0081h
Erase Config Bits	0082h
Erase Code EEPROM Block 0	0180h
Erase Code EEPROM Block 1	0280h
Erase Code EEPROM Block 2	0480h
Erase Code EEPROM Block 3	0880h

The actual Bulk Erase function is a self-timed operation. Once the erase has started (falling edge of the 4th PGC after the NOP command), serial execution will cease until the erase completes (parameter P11). During this time, PGC may continue to toggle but PGD must be held low.

The code sequence to erase the entire device is shown in Table 3-2 and the flowchart is shown in Figure 3-1.

Note:	A Bulk Erase is the only way to reprogram code-protect bits from an “on” state to an “off” state.

TABLE 3-2: BULK ERASE COMMAND SEQUENCE

4-Bit Command	Data Payload	Core Instruction
0000	0E 3C	MOVLW 3Ch
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPTRH
0000	0E 05	MOVLW 05h
0000	6E F6	MOVWF TBLPTRL
1100	0F 0F	Write 0Fh to 3C0005h
0000	0E 3C	MOVLW 3Ch
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPTRH
0000	0E 04	MOVLW 04h
0000	6E F6	MOVWF TBLPTRL
1100	8F 8F	Write 8F8Fh TO 3C0004h to erase entire device.
0000	00 00	NOP
0000	00 00	Hold PGD low until erase completes.

FIGURE 3-1: BULK ERASE FLOW

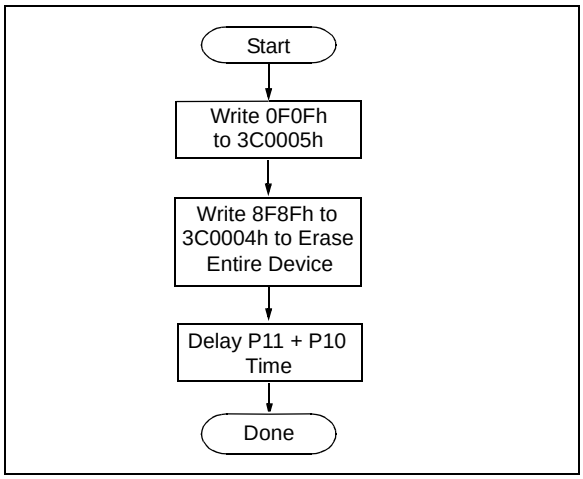
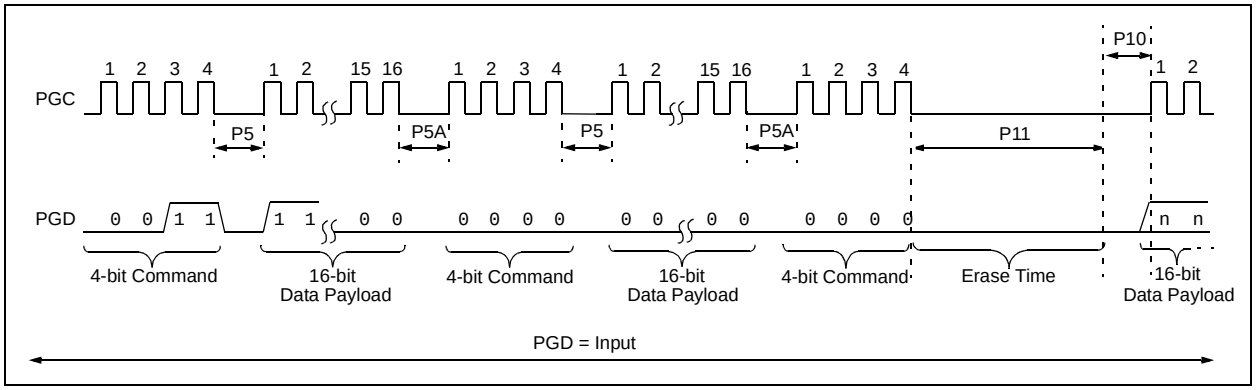


FIGURE 3-2: BULK ERASE TIMING DIAGRAM



3.1.2 LOW-VOLTAGE ICSP BULK ERASE

When using low-voltage ICSP, the part must be supplied by the voltage specified in parameter D111 if a Bulk Erase is to be executed. All other Bulk Erase details as described above apply.

If it is determined that a program memory erase must be performed at a supply voltage below the Bulk Erase limit, refer to the erase methodology described in **Section 3.1.3 "ICSP Row Erase"** and **Section 3.2.1 "Modifying Code Memory"**.

If it is determined that a data EEPROM erase must be performed at a supply voltage below the Bulk Erase limit, follow the methodology described in **Section 3.3 "Data EEPROM Programming"** and write '1's to the array.

3.1.3 ICSP ROW ERASE

Regardless of whether high or low-voltage ICSP is used, it is possible to erase one row (64 bytes of data), provided the block is not code or write-protected. Rows are located at static boundaries beginning at program memory address 000000h, extending to the internal program memory limit (see **Section 2.3 "Memory Maps"**).

The Row Erase duration is self-timed. After the WR bit in EECON1 is set, two NOPs are issued. Erase starts upon the 4th PGC of the second NOP. It ends when the WR bit is cleared by hardware.

The code sequence to Row Erase a PIC18F2XK20/4XK20 device is shown in Table 3-3. The flowchart shown in Figure 3-3 depicts the logic necessary to completely erase a PIC18F2XK20/4XK20 device. The timing diagram for Row Erase is identical to the data EEPROM write timing shown in Figure 3-7.

Note:	The TBLPTR register can point at any byte within the row intended for erase.

TABLE 3-3: ERASE CODE MEMORY CODE SEQUENCE

4-bit Command	Data Payload	Core Instruction
Step 1: Direct access to code memory and enable writes.		
0000	8E A6	BSF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
0000	84 A6	BSF EECON1, WREN
Step 2: Point to first row in code memory.		
0000	6A F8	CLRF TBLPTRU
0000	6A F7	CLRF TBLPTRH
0000	6A F6	CLRF TBLPTRL
Step 3: Enable erase and erase single row.		
0000	88 A6	BSF EECON1, FREE
0000	82 A6	BSF EECON1, WR
0000	00 00	NOP
0000	00 00	NOP Erase starts on the 4th clock of this instruction
Step 4: Poll WR bit. Repeat until bit is clear.		
0000	50 A6	MOVF EECON1, W, 0
0000	6E F5	MOVWF TABLAT
0000	00 00	NOP
0010	<MSB><LSB>	Shift out data(1)
Step 5: Hold PGC low for time P10.		
Step 6: Repeat step 3 with Address Pointer incremented by 64 until all rows are erased.		
Step 7: Disable writes.		
0000	94 A6	BCF EECON1, WREN

Note 1: See Figure 4-4 for details on shift out data timing.

FIGURE 3-4: PROGRAM CODE MEMORY FLOW

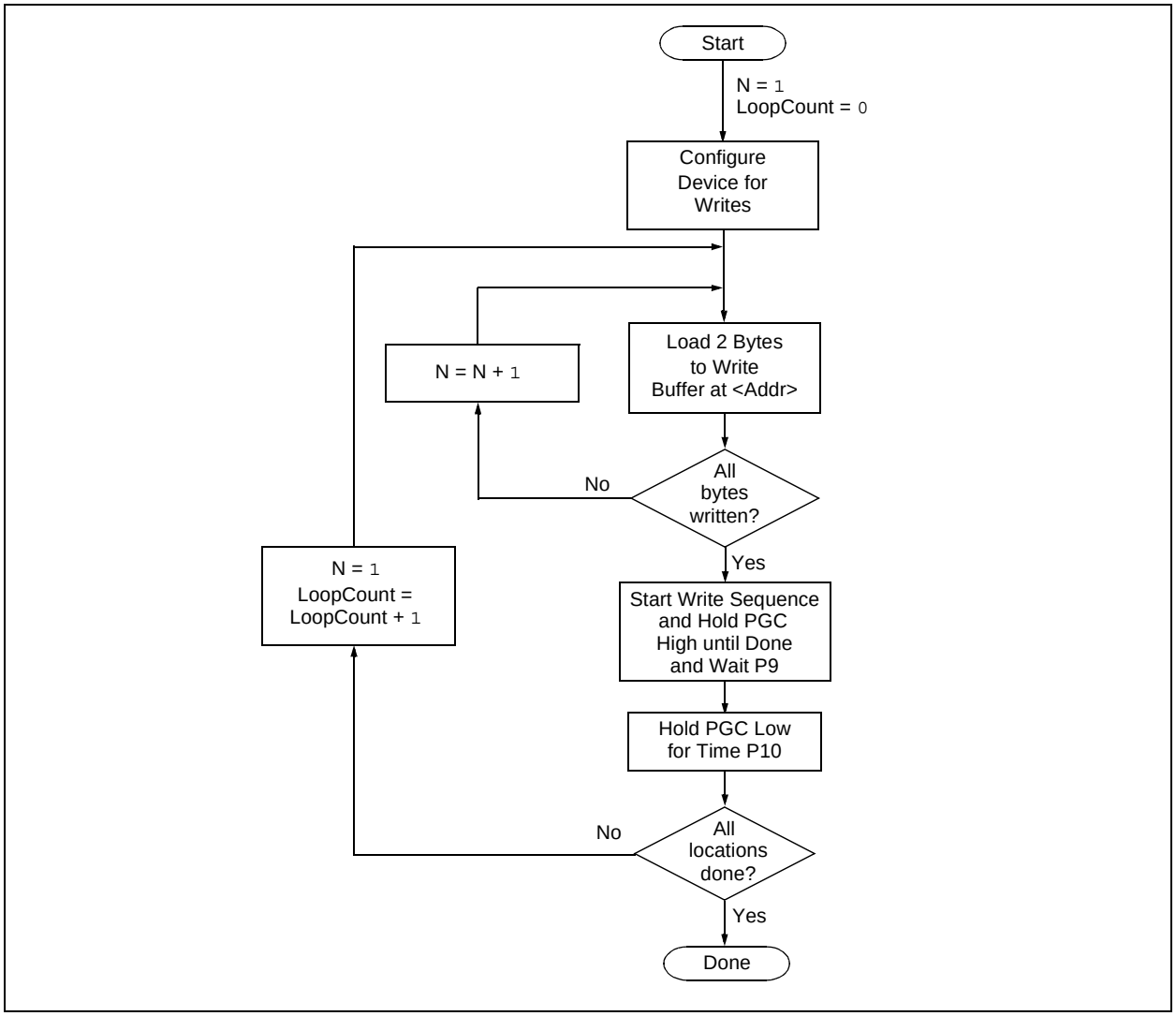
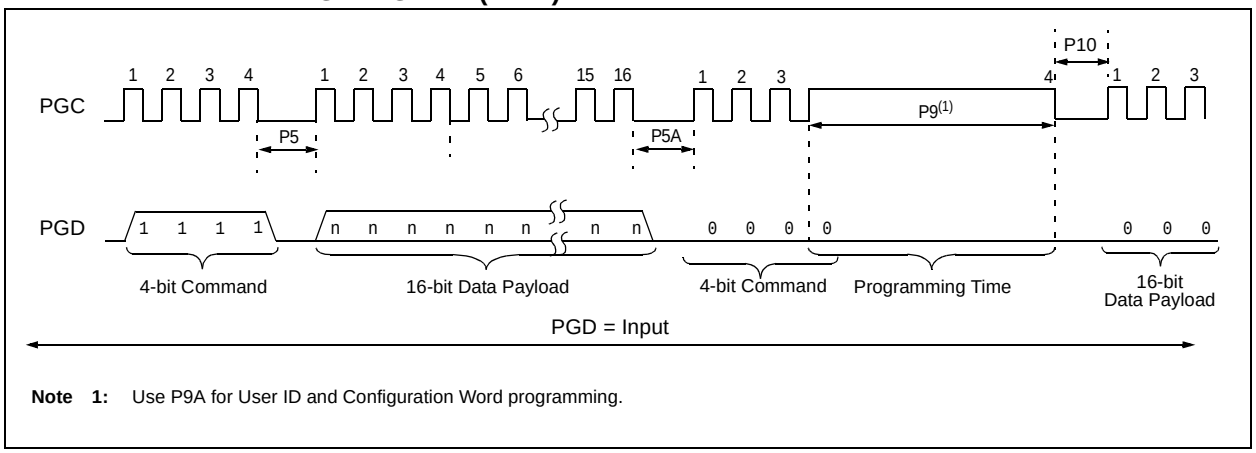


FIGURE 3-5: TABLE WRITE AND START PROGRAMMING INSTRUCTION TIMING DIAGRAM (1111)



Note 1: Use P9A for User ID and Configuration Word programming.

3.3 Data EEPROM Programming

Data EEPROM is accessed one byte at a time via an Address Pointer (register pair EEADRH:EEADR) and a data latch (EEDATA). Data EEPROM is written by loading EEADRH:EEADR with the desired memory location, EEDATA with the data to be written and initiating a memory write by appropriately configuring the EECON1 register. A byte write automatically erases the location and writes the new data (erase-before-write).

When using the EECON1 register to perform a data EEPROM write, both the EEPGD and CFGS bits must be cleared (EECON1<7:6> = 00). The WREN bit must be set (EECON1<2> = 1) to enable writes of any sort and this must be done prior to initiating a write sequence. The write sequence is initiated by setting the WR bit (EECON1<1> = 1).

The write begins on the falling edge of the 24th PGC after the WR bit is set. It ends when the WR bit is cleared by hardware.

After the programming sequence terminates, PGC must be held low for the time specified by parameter P10 to allow high-voltage discharge of the memory array.

FIGURE 3-6: PROGRAM DATA FLOW

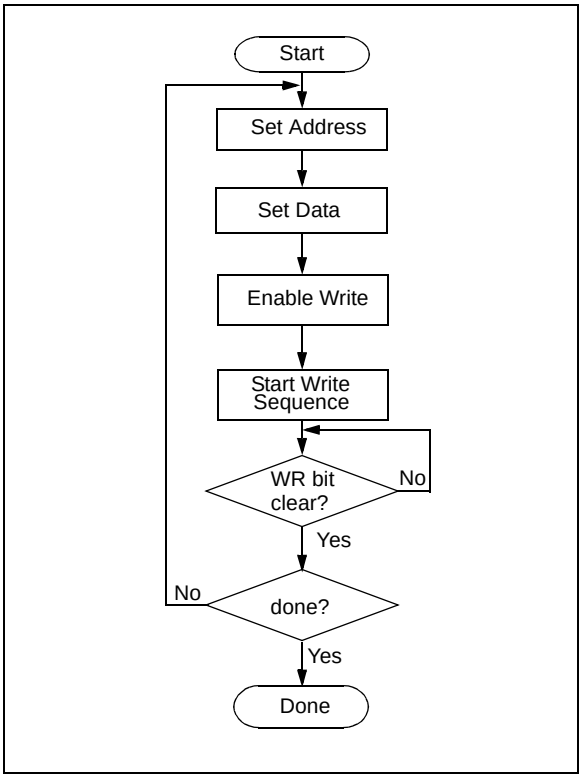


FIGURE 3-7: DATA EEPROM WRITE TIMING DIAGRAM

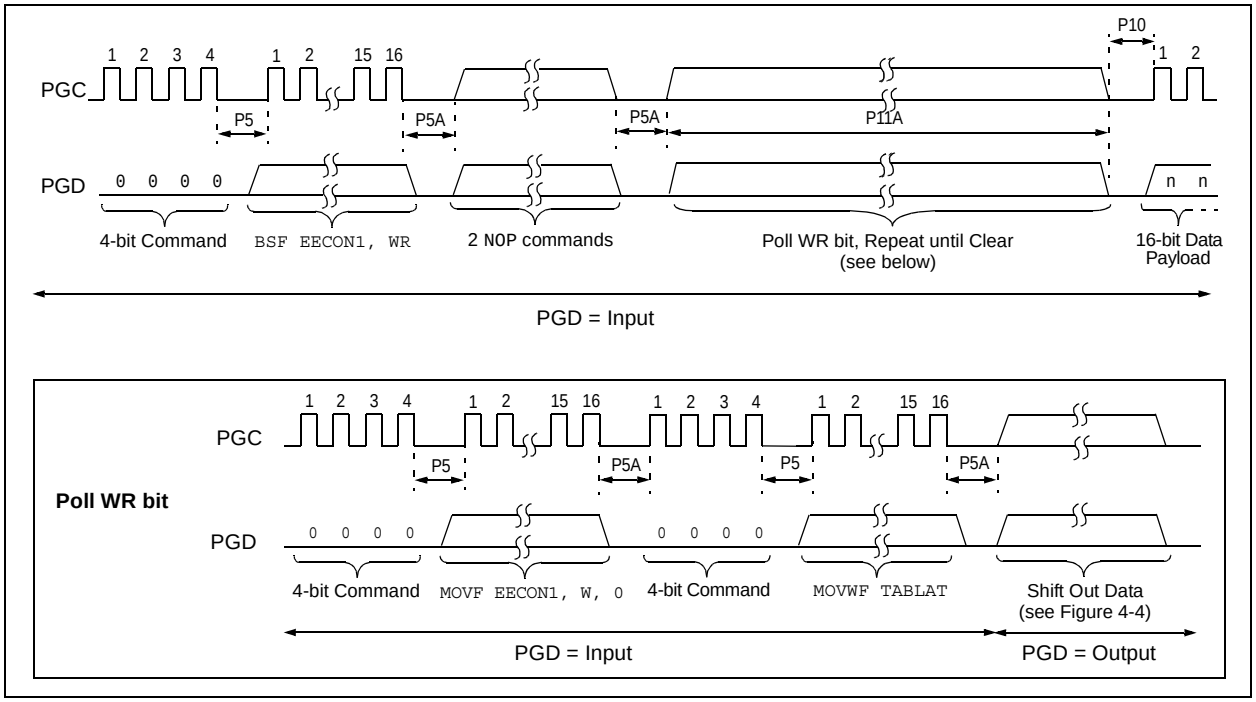


TABLE 3-7: PROGRAMMING DATA MEMORY

4-bit Command	Data Payload	Core Instruction
Step 1: Direct access to data EEPROM.		
0000	9E A6	BCF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
Step 2: Set the data EEPROM Address Pointer.		
0000	0E <Addr>	MOVLW <Addr>
0000	6E A9	MOVWF EEADR
0000	OE <AddrH>	MOVLW <AddrH>
0000	6E AA	MOVWF EEADRH
Step 3: Load the data to be written.		
0000	0E <Data>	MOVLW <Data>
0000	6E A8	MOVWF EEDATA
Step 4: Enable memory writes.		
0000	84 A6	BSF EECON1, WREN
Step 5: Initiate write.		
0000	82 A6	BSF EECON1, WR
0000	00 00	NOP
0000	00 00	NOP ;write starts on 4th clock of this instruction
Step 6: Poll WR bit, repeat until the bit is clear.		
0000	50 A6	MOVF EECON1, W, 0
0000	6E F5	MOVWF TABLAT
0000	00 00	NOP
0010	<MSB><LSB>	Shift out data(1)
Step 7: Hold PGC low for time P10.		
Step 8: Disable writes.		
0000	94 A6	BCF EECON1, WREN
Repeat steps 2 through 8 to write more data.		

Note 1: See Figure 4-4 for details on shift out data timing.

3.4 ID Location Programming

The ID locations are programmed much like the code memory. The ID registers are mapped in addresses 200000h through 200007h. These locations read out normally even after code protection.

Note:	The user only needs to fill the first 8 bytes of the write buffer in order to write the ID locations.

Table 3-8 demonstrates the code sequence required to write the ID locations.

In order to modify the ID locations, refer to the methodology described in **Section 3.2.1 "Modifying Code Memory"**. As with code memory, the ID locations must be erased before being modified.

When VDD is below the minimum for Bulk Erase operation, ID locations can be cleared with the Row Erase method described in **Section 3.1.3 "ICSP Row Erase"**.

TABLE 3-8: WRITE ID SEQUENCE

4-bit Command	Data Payload	Core Instruction
Step 1: Direct access to code memory.		
0000	8E A6	BSF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
0000	84 A6	BSF EECON1, WREN
Step 2: Set Table Pointer to ID. Load write buffer with 8 bytes and write.		
0000	0E 20	MOVLW 20h
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPTRH
0000	0E 00	MOVLW 00h
0000	6E F6	MOVWF TBLPTRL
1101	<MSB><LSB>	Write 2 bytes and post-increment address by 2.
1101	<MSB><LSB>	Write 2 bytes and post-increment address by 2.
1101	<MSB><LSB>	Write 2 bytes and post-increment address by 2.
1111	<MSB><LSB>	Write 2 bytes and start programming.
0000	00 00	NOP - hold PGC high for time P9 and low for time P10.

3.5 Boot Block Programming

The code sequence detailed in Table 3-5 should be used, except that the address used in “Step 2” will be in the range of 000000h to 0007FFh.

3.6 Configuration Bits Programming

Unlike code memory, the Configuration bits are programmed a byte at a time. The Table Write, Begin Programming 4-bit command (‘1111’) is used, but only 8 bits of the following 16-bit payload will be written. The LSB of the payload will be written to even addresses and the MSB will be written to odd addresses. The code sequence to program two consecutive configuration locations is shown in Table 3-9. See Figure 3-5 for the timing diagram.

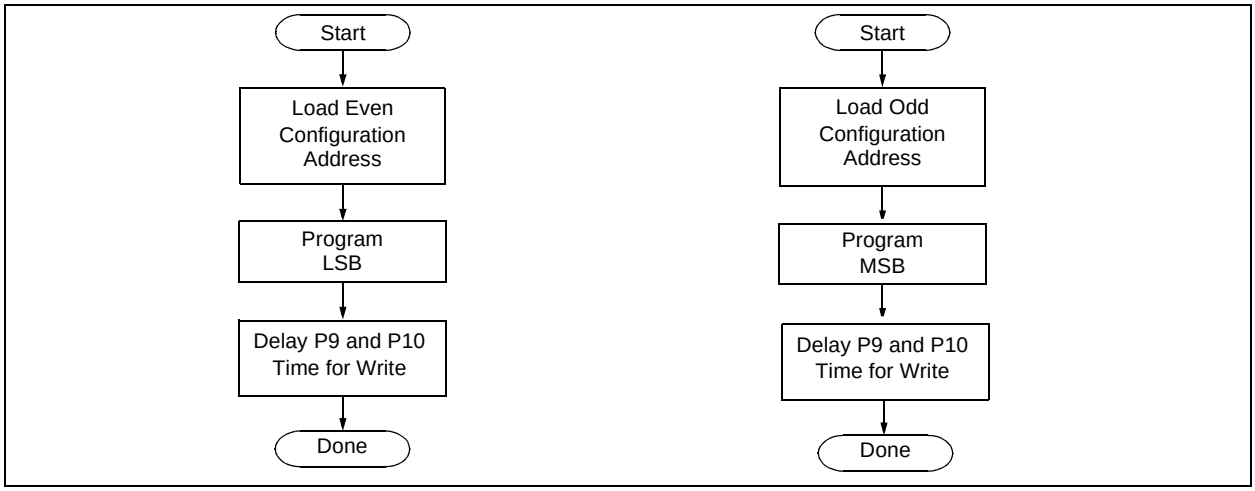
Note:	The address must be explicitly written for each byte programmed. The addresses can not be incremented in this mode.

TABLE 3-9: SET ADDRESS POINTER TO CONFIGURATION LOCATION

4-bit Command	Data Payload	Core Instruction
Step 1: Direct access to config memory.		
0000	8E A6	BSF EECON1, EEPGD
0000	8C A6	BSF EECON1, CFGS
0000	84 A6	BSF EECON1, WREN
Step 2(1): Set Table Pointer for config byte to be written. Write even/odd addresses.		
0000	0E 30	MOVLW 30h
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPRTH
0000	0E 00	MOVLW 00h
0000	6E F6	MOVWF TBLPTRL
1111	<MSB ignored><LSB>	Load 2 bytes and start programming.
0000	00 00	NOP - hold PGC high for time P9 and low for time P10.
0000	0E 01	MOVLW 01h
0000	6E F6	MOVWF TBLPTRL
1111	<MSB><LSB ignored>	Load 2 bytes and start programming.
0000	00 00	NOP - hold PGC high for time P9A and low for time P10.

Note 1: Enabling the write protection of Configuration bits (WRTC = 0 in CONFIG6H) will prevent further writing of Configuration bits. Always write all the Configuration bits before enabling the write protection for Configuration bits.

FIGURE 3-8: CONFIGURATION PROGRAMMING FLOW



4.3 Verify Configuration Bits

A configuration address may be read and output on PGD via the 4-bit command, '1001'. Configuration data is read and written in a byte-wise fashion, so it is not necessary to merge two bytes into a word prior to a compare. The result may then be immediately compared to the appropriate configuration data in the programmer's memory for verification. Refer to **Section 4.1 "Read Code Memory, ID Locations and Configuration Bits"** for implementation details of reading configuration data.

4.4 Read Data EEPROM Memory

Data EEPROM is accessed one byte at a time via an Address Pointer (register pair EEADRH:EEADR) and a data latch (EEDATA). Data EEPROM is read by loading EEADRH:EEADR with the desired memory location and initiating a memory read by appropriately configuring the EECON1 register. The data will be loaded into EEDATA, where it may be serially output on PGD via the 4-bit command, '0010' (Shift Out Data Holding register). A delay of P6 must be introduced after the falling edge of the 8th PGC of the operand to allow PGD to transition from an input to an output. During this time, PGC must be held low (see Figure 4-4).

The command sequence to read a single byte of data is shown in Table 4-2.

FIGURE 4-3: READ DATA EEPROM FLOW

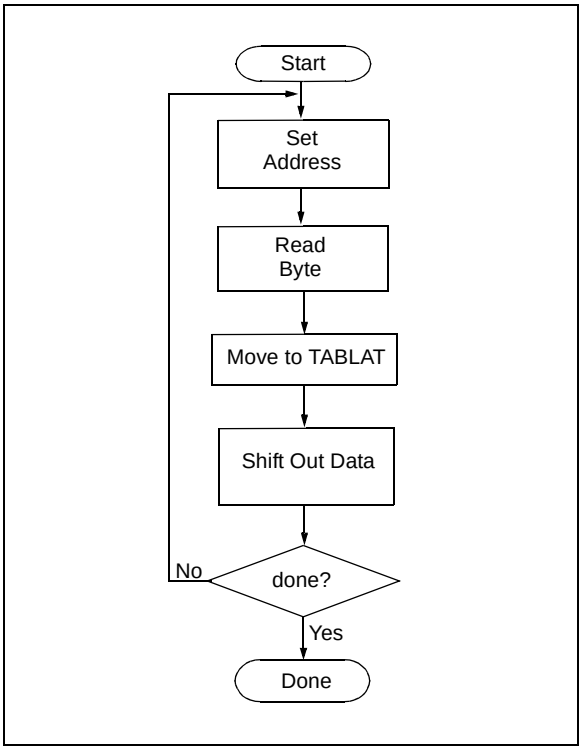


TABLE 4-2: READ DATA EEPROM MEMORY

4-bit Command	Data Payload	Core Instruction
Step 1: Direct access to data EEPROM.		
0000	9E A6	BCF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
Step 2: Set the data EEPROM Address Pointer.		
0000	0E <Addr>	MOVLW <Addr>
0000	6E A9	MOVWF EEADR
0000	OE <AddrH>	MOVLW <AddrH>
0000	6E AA	MOVWF EEADRH
Step 3: Initiate a memory read.		
0000	80 A6	BSF EECON1, RD
Step 4: Load data into the Serial Data Holding register.		
0000	50 A8	MOVF EEDATA, W, 0
0000	6E F5	MOVWF TABLAT
0000	00 00	NOP
0010	<MSB><LSB>	Shift Out Data(1)

Note 1: The <LSB> is undefined. The <MSB> is the data.

TABLE 5-2: DEVICE ID VALUE

Device	Device ID Value	
	DEVID2	DEVID1
PIC18F23K20	20h	111x xxxx
PIC18F24K20	20h	101x xxxx
PIC18F25K20	20h	011x xxxx
PIC18F26K20	20h	001x xxxx
PIC18F43K20	20h	110x xxxx
PIC18F44K20	20h	100x xxxx
PIC18F45K20	20h	010x xxxx
PIC18F46K20	20h	000x xxxx

Note: The ‘x’s in DEVID1 contain the device revision code.

TABLE 5-3: PIC18F2XK20/4XK20 BIT DESCRIPTIONS

Bit Name	Configuration Words	Description
IESO	CONFIG1H	Internal External Switchover bit 1 = Internal External Switchover mode enabled 0 = Internal External Switchover mode disabled
FCMEN	CONFIG1H	Fail-Safe Clock Monitor Enable bit 1 = Fail-Safe Clock Monitor enabled 0 = Fail-Safe Clock Monitor disabled
FOSC<3:0>	CONFIG1H	Oscillator Selection bits 11xx = External RC oscillator, CLKOUT function on RA6 101x = External RC oscillator, CLKOUT function on RA6 1001 = HFINTOSC, CLKOUT function on RA6, port function on RA7 1000 = HFINTOSC, port function on RA6, port function on RA7 0111 = External RC oscillator, port function on RA6 0110 = HS oscillator, PLL enabled (clock frequency = 4 x FOSC1) 0101 = EC oscillator, port function on RA6 0100 = EC oscillator, CLKOUT function on RA6 0011 = External RC oscillator, CLKOUT function on RA6 0010 = HS oscillator 0001 = XT oscillator 0000 = LP oscillator
BORV<1:0>	CONFIG2L	Brown-out Reset Voltage bits 11 = V_{BOR} set to 1.8V 10 = V_{BOR} set to 2.2V 01 = V_{BOR} set to 2.7V 00 = V_{BOR} set to 3.0V
BOREN<1:0>	CONFIG2L	Brown-out Reset Enable bits 11 = Brown-out Reset enabled in hardware only (SBOREN is disabled) 10 = Brown-out Reset enabled in hardware only and disabled in Sleep mode (SBOREN is disabled) 01 = Brown-out Reset enabled and controlled by software (SBOREN is enabled) 00 = Brown-out Reset disabled in hardware and software
PWRTEN	CONFIG2L	Power-up Timer Enable bit 1 = PWRT disabled 0 = PWRT enabled
WDPS<3:0>	CONFIG2H	Watchdog Timer Postscaler Select bits 1111 = 1:32,768 1110 = 1:16,384 1101 = 1:8,192 1100 = 1:4,096 1011 = 1:2,048 1010 = 1:1,024 1001 = 1:512 1000 = 1:256 0111 = 1:128 0110 = 1:64 0101 = 1:32 0100 = 1:16 0011 = 1:8 0010 = 1:4 0001 = 1:2 0000 = 1:1

.

TABLE 5-3: PIC18F2XK20/4XK20 BIT DESCRIPTIONS (CONTINUED)

Bit Name	Configuration Words	Description
WDTEN	CONFIG2H	Watchdog Timer Enable bit 1 = WDT enabled 0 = WDT disabled (control is placed on SWDTEN bit)
MCLRE	CONFIG3H	$\overline{\text{MCLR}}$ Pin Enable bit 1 = $\overline{\text{MCLR}}$ pin enabled, RE3 input pin disabled 0 = RE3 input pin enabled, $\overline{\text{MCLR}}$ pin disabled
HFOFST	CONFIG3H	HFINTOSC Fast Start 1 = HFINTOSC output is not delayed 0 = HFINTOSC output is delayed until oscillator is stable (IOFS = 1)
LPT1OSC	CONFIG3H	Low-Power Timer1 Oscillator Enable bit 1 = Timer1 configured for low-power operation 0 = Timer1 configured for higher power operation
PBADEN	CONFIG3H	PORTB A/D Enable bit 1 = PORTB A/D<4:0> pins are configured as analog input channels on Reset 0 = PORTB A/D<4:0> pins are configured as digital I/O on Reset
CCP2MX	CONFIG3H	CCP2 MUX bit 1 = CCP2 input/output is multiplexed with RC1 0 = CCP2 input/output is multiplexed with RB3
DEBUG	CONFIG4L	Background Debugger Enable bit 1 = Background debugger disabled, RB6 and RB7 configured as general purpose I/O pins 0 = Background debugger enabled, RB6 and RB7 are dedicated to In-Circuit Debug
XINST	CONFIG4L	Extended Instruction Set Enable bit 1 = Instruction set extension and Indexed Addressing mode enabled 0 = Instruction set extension and Indexed Addressing mode disabled (Legacy mode)
LVP	CONFIG4L	Low-Voltage Programming Enable bit 1 = Low-Voltage Programming enabled, RB5 is the PGM pin 0 = Low-Voltage Programming disabled, RB5 is an I/O pin
STVREN	CONFIG4L	Stack Overflow/Underflow Reset Enable bit 1 = Reset on stack overflow/underflow enabled 0 = Reset on stack overflow/underflow disabled

.

TABLE 5-4: CHECKSUM COMPUTATION

Device	Code-Protect	Checksum	Blank Value	0xAA at 0 and Max Address
PIC18FX3K20	None	SUM[0000:01FF]+SUM[0200:0FFF]+SUM[1000:1FFF]+ (CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)	E33Eh	E294h
	Boot Block	SUM[0200:0FFF]+SUM[1000:1FFF]+(CONFIG1L & 00h)+ (CONFIG1H & CFh)+(CONFIG2L & 1Fh)+(CONFIG2H & 1F)+ (CONFIG3L & 00h)+(CONFIG3H & 8Fh)+(CONFIG4L & C5h)+ (CONFIG4H & 00h)+(CONFIG5L & 03h)+(CONFIG5H & C0h)+ (CONFIG6L & 03h)+(CONFIG6H & E0h)+(CONFIG7L & 03h)+ (CONFIG7H & 40h)+SUM_ID	E520h	E4C6h
	Boot/ Block 0	SUM[1000:1FFF]+(CONFIG1L & 00h)+(CONFIG1H & CFh)+ (CONFIG2L & 1Fh)+(CONFIG2H & 1F)+(CONFIG3L & 00h)+ (CONFIG3H & 8Fh)+(CONFIG4L & C5h)+(CONFIG4H & 00h)+ (CONFIG5L & 03h)+(CONFIG5H & C0h)+(CONFIG6L & 03h)+ (CONFIG6H & E0h)+(CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	F31Fh	F2C5h
	All	(CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	031Dh	0318h
PIC18FX4K20	None	SUM[0000:07FF]+SUM[0800:1FFF]+SUM[2000:3FFF]+ (CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)	C33Eh	C294h
	Boot Block	SUM[0800:1FFF]+SUM[2000:3FFF]+(CONFIG1L & 00h)+ (CONFIG1H & CFh)+(CONFIG2L & 1Fh)+(CONFIG2H & 1F)+ (CONFIG3L & 00h)+(CONFIG3H & 8Fh)+(CONFIG4L & C5h)+ (CONFIG4H & 00h)+(CONFIG5L & 03h)+(CONFIG5H & C0h)+ (CONFIG6L & 03h)+(CONFIG6H & E0h)+(CONFIG7L & 03h)+ (CONFIG7H & 40h)+SUM_ID	CB1Eh	CAC4h
	Boot/ Block 0	SUM[2000:3FFF]+(CONFIG1L & 00h)+(CONFIG1H & CFh)+ (CONFIG2L & 1Fh)+(CONFIG2H & 1F)+(CONFIG3L & 00h)+ (CONFIG3H & 8Fh)+(CONFIG4L & C5h)+(CONFIG4H & 00h)+ (CONFIG5L & 03h)+(CONFIG5H & C0h)+(CONFIG6L & 03h)+ (CONFIG6H & E0h)+(CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	E31Dh	E2C3h
	All	(CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 03h)+ (CONFIG5H & C0h)+(CONFIG6L & 03h)+(CONFIG6H & E0h)+ (CONFIG7L & 03h)+(CONFIG7H & 40h)+SUM_ID	031Bh	0316h

Legend:

Item		Description
CONFIGx	=	Configuration Word
SUM[a:b]	=	Sum of locations, a to b inclusive
SUM_ID	=	Byte-wise sum of lower four bits of all customer ID locations
+	=	Addition
&	=	Bit-wise AND

TABLE 5-4: CHECKSUM COMPUTATION (CONTINUED)

Device	Code-Protect	Checksum	Blank Value	0xAA at 0 and Max Address
PIC18FX5K20	None	SUM[0000:07FF]+SUM[0800:1FFF]+SUM[2000:3FFF]+ SUM[4000:5FFF]+SUM[6000:7FFF]+(CONFIG1L & 00h)+ (CONFIG1H & CFh)+(CONFIG2L & 1Fh)+(CONFIG2H & 1F)+ (CONFIG3L & 00h)+(CONFIG3H & 8Fh)+(CONFIG4L & C5h)+ (CONFIG4H & 00h)+(CONFIG5L & 0Fh)+(CONFIG5H & C0h)+ (CONFIG6L & 0Fh)+(CONFIG6H & E0h)+(CONFIG7L & 0Fh)+ (CONFIG7H & 40h)	8362h	82B8h
	Boot Block	SUM[0800:1FFF]+SUM[2000:3FFF]+SUM[4000:5FFF]+SUM[6000:7FFF]+ (CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 0Fh)+ (CONFIG5H & C0h)+(CONFIG6L & 0Fh)+(CONFIG6H & E0h)+ (CONFIG7L & 0Fh)+(CONFIG7H & 40h)+SUM_ID	8B35h	8AEAh
	Boot/ Block 0/ Block 1	SUM[4000:5FFF]+SUM[6000:7FFF]+(CONFIG1L & 00h)+ (CONFIG1H & CFh)+(CONFIG2L & 1Fh)+(CONFIG2H & 1F)+ (CONFIG3L & 00h)+(CONFIG3H & 8Fh)+(CONFIG4L & C5h)+ (CONFIG4H & 00h)+(CONFIG5L & 0Fh)+(CONFIG5H & C0h)+ (CONFIG6L & 0Fh)+(CONFIG6H & E0h)+(CONFIG7L & 0Fh)+ (CONFIG7H & 40h)+SUM_ID	C332h	C2E7h
	All	(CONFIG1L & 00h)+(CONFIG1H & CFh)+(CONFIG2L & 1Fh)+ (CONFIG2H & 1F)+(CONFIG3L & 00h)+(CONFIG3H & 8Fh)+ (CONFIG4L & C5h)+(CONFIG4H & 00h)+(CONFIG5L & 0Fh)+ (CONFIG5H & C0h)+(CONFIG6L & 0Fh)+(CONFIG6H & E0h)+ (CONFIG7L & 0Fh)+(CONFIG7H & 40h)+SUM_ID	0326h	0330h

Legend:

Item		Description
CONFIGx	=	Configuration Word
SUM[a:b]	=	Sum of locations, a to b inclusive
SUM_ID	=	Byte-wise sum of lower four bits of all customer ID locations
+	=	Addition
&	=	Bit-wise AND

6.0 AC/DC CHARACTERISTICS TIMING REQUIREMENTS FOR PROGRAM/ VERIFY TEST MODE

Standard Operating Conditions
Operating Temperature: 25°C is recommended

Param No.	Sym.	Characteristic	Min.	Max.	Units	Conditions
D110	VIHH	High-Voltage Programming Voltage on MCLR/VPP/RE3	VDD + 4.5	9	V	
D110A	VIHL	Low-Voltage Programming Voltage on MCLR/VPP/RE3	1.80	3.60	V	
D111	VDD	Supply Voltage During Programming	1.80	3.60	V	Row Erase/Write
			2.7	3.60	V	Bulk Erase operations
D112	IPP	Programming Current on MCLR/VPP/RE3	—	300	μA	
D113	IDDP	Supply Current During Programming	—	10	mA	
D031	VIL	Input Low Voltage	VSS	0.2 VDD	V	
D041	VIH	Input High Voltage	0.8 VDD	VDD	V	
D080	VOL	Output Low Voltage	—	0.6	V	IOL = X.X mA @ 2.7V
D090	VOH	Output High Voltage	VDD – 0.7	—	V	IOH = -Y.Y mA @ 2.7V
D012	CIO	Capacitive Loading on I/O pin (PGD)	—	50	pF	To meet AC specifications
P1	TR	MCLR/VPP/RE3 Rise Time to enter Program/Verify mode	—	1.0	μs	**(Note 1)**
P2	TPGC	Serial Clock (PGC) Period	100	—	ns	VDD = 3.6V
			1	—	μs	VDD = 1.8V
P2A	TPGCL	Serial Clock (PGC) Low Time	40	—	ns	VDD = 3.6V
			400	—	ns	VDD = 1.8V
P2B	TPGCH	Serial Clock (PGC) High Time	40	—	ns	VDD = 3.6V
			400	—	ns	VDD = 1.8V
P3	TSET1	Input Data Setup Time to Serial Clock ↓	15	—	ns	
P4	THLD1	Input Data Hold Time from PGC ↓	15	—	ns	
P5	TDLY1	Delay between 4-bit Command and Command Operand	40	—	ns	
P5A	TDLY1A	Delay between 4-bit Command Operand and next 4-bit Command	40	—	ns	
P6	TDLY2	Delay between Last PGC ↓ of Command Byte to First PGC ↑ of Read of Data Word	20	—	ns	
P9	TDLY5	PGC High Time (minimum programming time)	1	—	ms	Externally Timed
P9A	TDLY5A	PGC High Time	5		ms	Configuration Word programming time
P10	TDLY6	PGC Low Time after Programming (high-voltage discharge time)	200	—	μs	
P11	TDLY7	Delay to allow Self-Timed Data Write or Bulk Erase to occur	5	—	ms	
P11A	TDRWT	Data Write Polling Time	4	—	ms	

Note 1: Do not allow excess time when transitioning MCLR between VIL and VIHH; this can cause spurious program executions to occur. The maximum transition time is:
1 TCY + TPWRT (if enabled) + 1024 TOSC (for LP, HS, HS/PLL and XT modes only) + 2 ms (for HS/PLL mode only) + 1.5 μs (for EC mode only) where TCY is the instruction cycle time, TPWRT is the Power-up Timer period and TOSC is the oscillator period. For specific values, refer to the Electrical Characteristics section of the device data sheet for the particular device.

6.0 AC/DC CHARACTERISTICS TIMING REQUIREMENTS FOR PROGRAM/ VERIFY TEST MODE (CONTINUED)

Standard Operating Conditions
Operating Temperature: 25°C is recommended

Param No.	Sym.	Characteristic	Min.	Max.	Units	Conditions
P12	THLD2	Input Data Hold Time from $\overline{MCLR}$/VPP/RE3 ↑	2	—	µs	
P13	TSET2	VDD ↑ Setup Time to $\overline{MCLR}$/VPP/RE3 ↑	100	—	ns	
P14	TVALID	Data Out Valid from PGC ↑	10	—	ns	
P15	TSET3	PGM ↑ Setup Time to $\overline{MCLR}$/VPP/RE3 ↑	2	—	µs	
P16	TDLY8	Delay between Last PGC ↓ and $\overline{MCLR}$/VPP/RE3 ↓	0	—	s	
P17	THLD3	$\overline{MCLR}$/VPP/RE3 ↓ to VDD ↓	—	100	ns	
P18	THLD4	$\overline{MCLR}$/VPP/RE3 ↓ to PGM ↓	0	—	s	
P19	THIZ	Delay from PGC ↑ to PGD High-Z	3	10	nS	
P20	TPPDP	Hold time after VPP changes	5	—	µs	

Note 1: Do not allow excess time when transitioning $\overline{MCLR}$ between VIL and VIHH; this can cause spurious program executions to occur. The maximum transition time is:
1 TCY + TPWRT (if enabled) + 1024 TOSC (for LP, HS, HS/PLL and XT modes only) + 2 ms (for HS/PLL mode only) + 1.5 µs (for EC mode only) where TCY is the instruction cycle time, TPWRT is the Power-up Timer period and TOSC is the oscillator period. For specific values, refer to the Electrical Characteristics section of the device data sheet for the particular device.

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